AMENDMENTS TO THE SPECIFICATION

Please amend page 7, line 20 to page 8, line 6 as follows:

During ~~a~~ an insulation layer 26 etch process, fluorine (F) containing plasma gas such as C_2F_4, C_2F_6, C_3F_8, C_4F_6, C_5F_8 or C_6F_6, i.e., C_xF_y, wherein x and y ranges from 1 to 10 is generally used as a main etching gas during the SAC process. Herein, such gas for generating a polymer during the SAC process, i.e., CH_2F_2, C_3HF_5 or CHF_3 is also added thereto. At this time, an inert gas such as helium (He), neon (Ne), argon (Ar) or xenon (Xe) is used as a carrier gas. Accordingly, it is possible to obtain an etching profile of the SAC process capable of minimizing damage of a gate hard mask 23 by protecting an upper area of the gate hard mask 23. Next, the photo-resist pattern and etching remnants are removed by performing a photo-resist strip process and a cleaning process, respectively.